

- ★ Green Device Available
- ★ Super Low Gate Charge
- ★ Advanced high cell density Trench technology
- ★ 100% EAS Guaranteed
- ★ Excellent CdV/dt effect decline

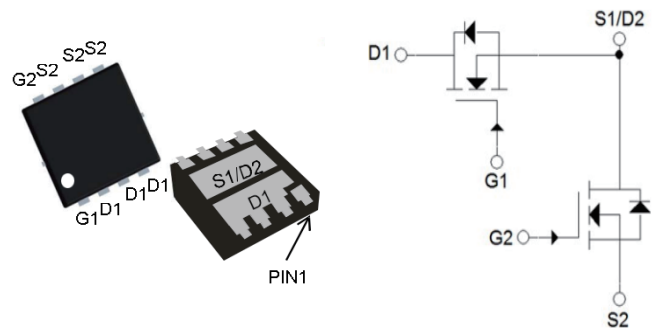
Product Summary

BVDSS	R _{DS(on)}	I _D
40V	6.9mΩ	40A

Description

The S60J04F is the high cell density trenched N-ch MOSFETs, which provide excellent R_{DS(on)} and gate charge for most of the synchronous buck converter applications. The S60J04F meet the RoHS and Green Product requirement, 100% EAS guaranteed with full function reliability approved.

PDFN5*6-8L Pin Configuration



Absolute Maximum Ratings

Symbol	Parameter	Rating	Unit
V _{DS}	Drain-Source Voltage	40	V
V _{GS}	Gate-Source Voltage	±20	V
I _{D@Tc=25°C}	Continuous Drain Current ₁	40	A
I _{D@Tc=100°C}	Continuous Drain Current ₁	25	A
I _{DM}	Pulsed Drain Current ₂	100	A
EAS	Single Pulse Avalanche Energy ₃	28	mJ
I _{AS}	Avalanche Current	40	A
P _{D@Tc=25°C}	Total Power Dissipation ₄	29	W
T _{STG}	Storage Temperature Range	-55 to 150	°C
T _J	Operating Junction Temperature Range	-55 to 150	°C

Thermal Data

Symbol	Parameter	Typ.	Max.	Units
R _{θJA}	Thermal Resistance Junction-ambient (Steady State) ₁	---	60	°C/W
R _{θJC}	Thermal Resistance Junction-Case ₁	---	3.2	°C/W

Electrical Characteristics ($T_J = 25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter	Test condition	Min.	Typ.	Max.	Units
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=250\mu A$	40	---	---	V
$R_{DS(ON)}$	Static Drain-Source On-Resistance ²	$V_{GS}=10V, I_D=12A$	---	6.9	8.5	m Ω
		$V_{GS}=4.5V, I_D=10A$	---	10	15	
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS}=V_{DS}, I_D=250\mu A$	1.35	---	3	V
I_{DSS}	Drain-Source Leakage Current	$V_{DS}=32V, V_{GS}=0V, T_J=25^\circ\text{C}$	---	---	1	μA
		$V_{DS}=32V, V_{GS}=0V, T_J=55^\circ\text{C}$	---	---	5	
I_{GSS}	Gate-Source Leakage Current	$V_{GS}=\pm 20V, V_{DS}=0V$	---	---	± 100	nA
R_g	Gate Resistance	$V_{DS}=0V, V_{GS}=0V, f=1\text{MHz}$	---	1.7	---	Ω
Q_g	Total Gate Charge (4.5V)	$V_{DS}=20V, V_{GS}=4.5V, I_D=12A$	---	5.8	---	nC
Q_{gs}	Gate-Source Charge		---	3	---	
Q_{gd}	Gate-Drain Charge		---	1.2	---	
$T_{d(on)}$	Turn-On Delay Time	$V_{DD}=15V, V_{GS}=10V, R_G=3.3\Omega, I_D=1A$	---	14.3	---	ns
T_r	Rise Time		---	5.6	---	
$T_{d(off)}$	Turn-Off Delay Time		---	20	---	
T_f	Fall Time		---	11	---	
C_{iss}	Input Capacitance	$V_{DS}=15V, V_{GS}=0V, f=1\text{MHz}$	---	690	---	pF
C_{oss}	Output Capacitance		---	193	---	
C_{rss}	Reverse Transfer Capacitance		---	38	---	

Thermal Data

Symbol	Parameter	Test condition	Min.	Typ.	Max.	Units
I_S	Continuous Source Current ^{1,5}	$V_G=V_D=0V$, Force Current	---	---	40	A
V_{SD}	Diode Forward Voltage ²	$V_{GS}=0V, I_S=1A, T_J=25^\circ\text{C}$	---	---	1	V

Note :

- 1.The data tested by surface mounted on a 1 inch² FR-4 board with 20Z copper.
- 2.The data tested by pulsed , pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$
- 3.The EAS data shows Max. rating . The test condition is $V_{DD}=25V, V_{GS}=10V, L=0.1mH, I_{AS}=31A$
- 4.The power dissipation is limited by 150°C junction temperature
- 5.The data is theoretically the same as I_D and I_{DM} , in real applications , should be limited by total power dissipation.

Typical Performance Characteristics

Figure1: Output Characteristics

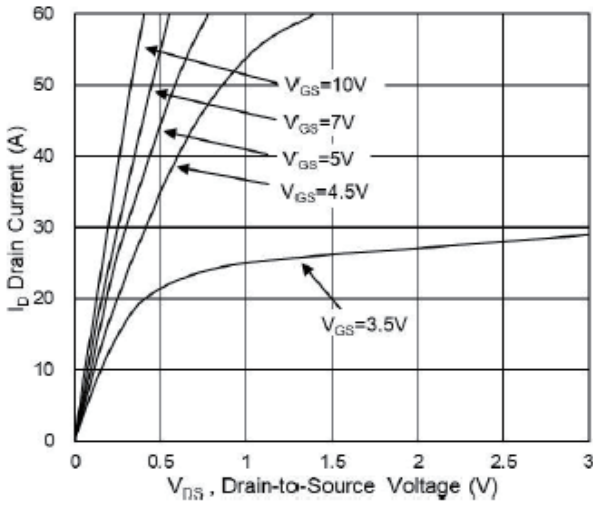


Figure 2: On-Resistance vs G-S Voltage

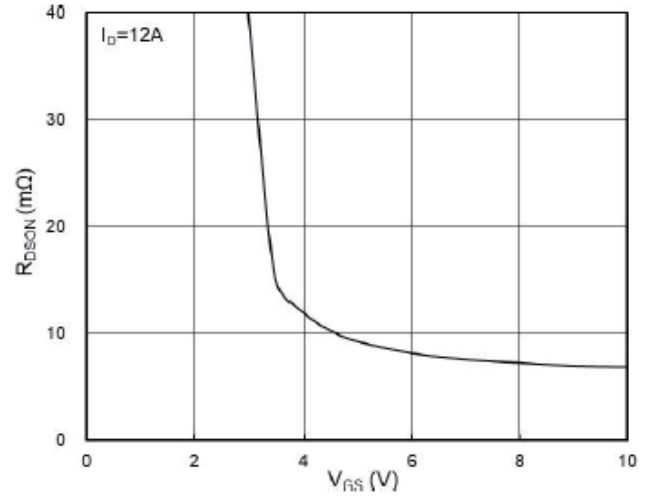


Figure 3: Source Drain Forward Character

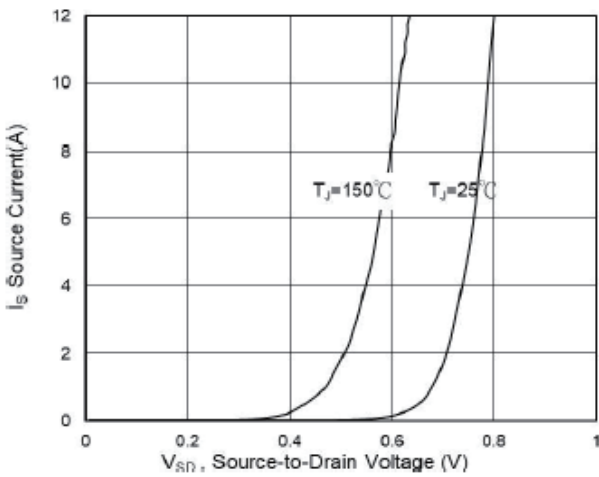


Figure 4: Gate-Charge Characteristics

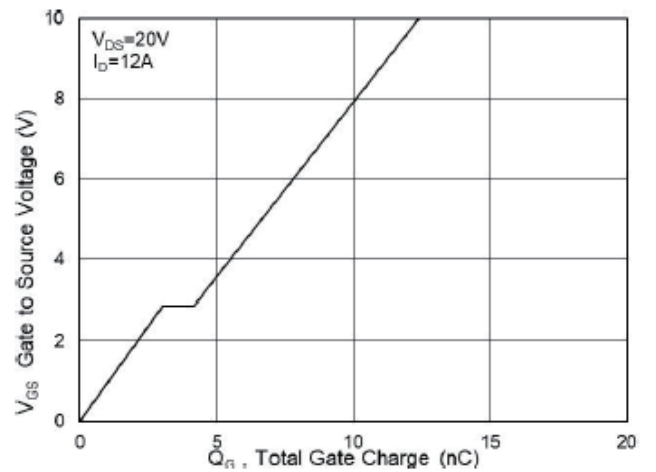


Figure 5: Normalized VGS(th) vs TJ Fig.6

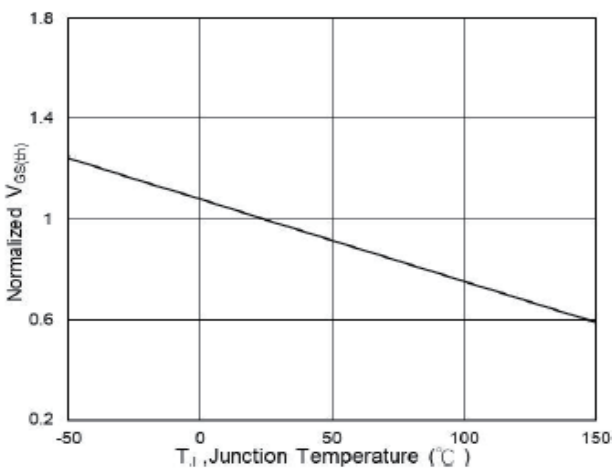
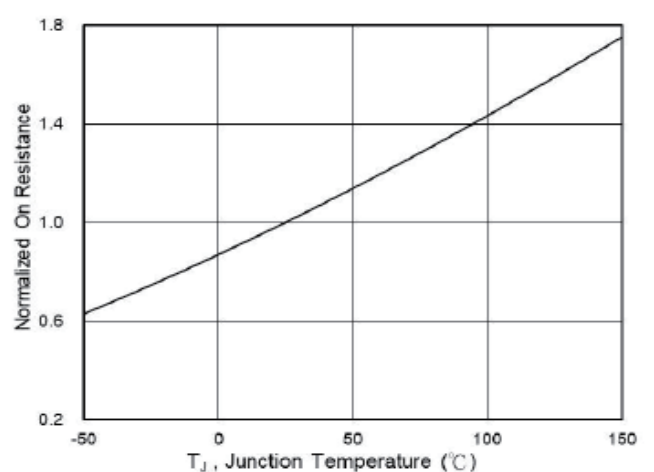


Figure 6: Normalized RDS(on) vs TJ



Typical Performance Characteristics

Figure 7: Capacitance

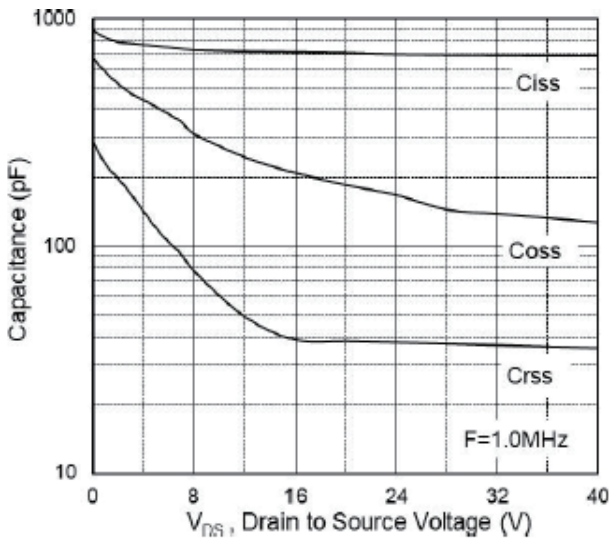


Figure 8: Safe Operating Area

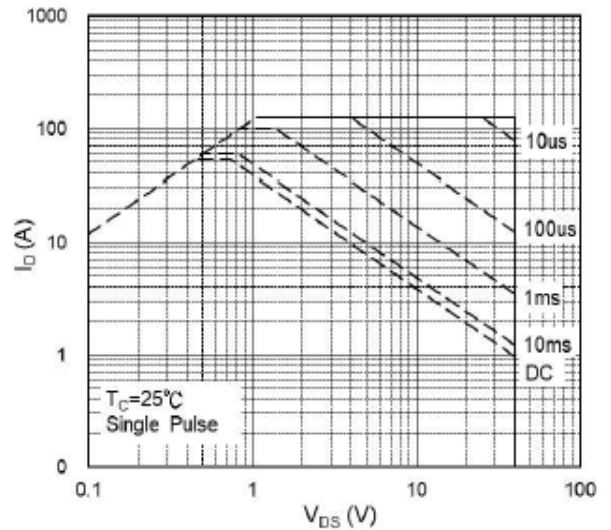


Figure 9: Normalized Maximum Transient Thermal Impedance

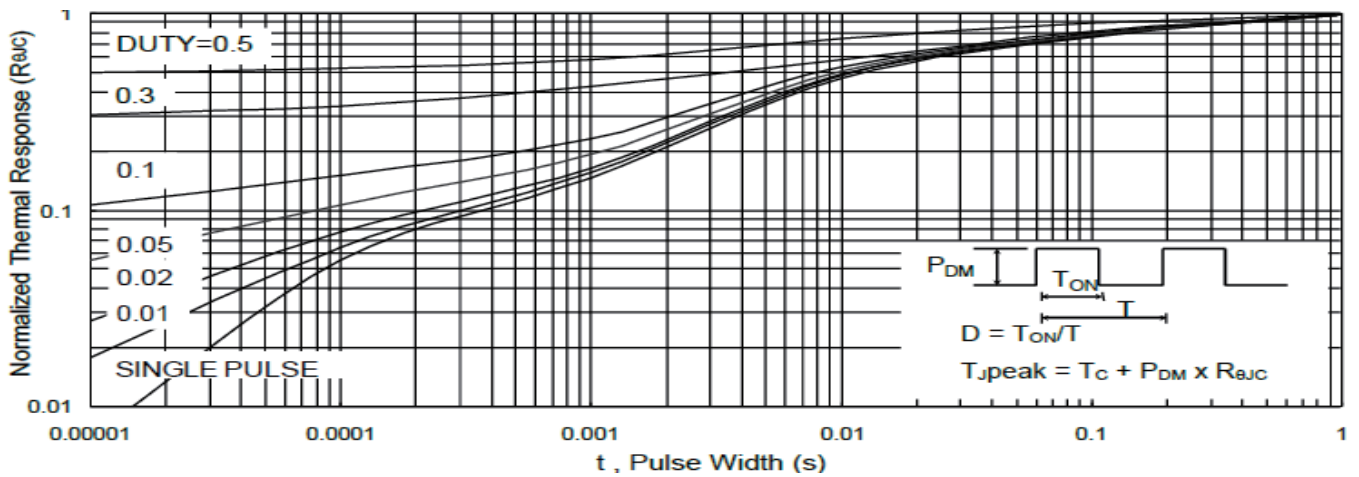


Figure.10: Switching Time Waveform

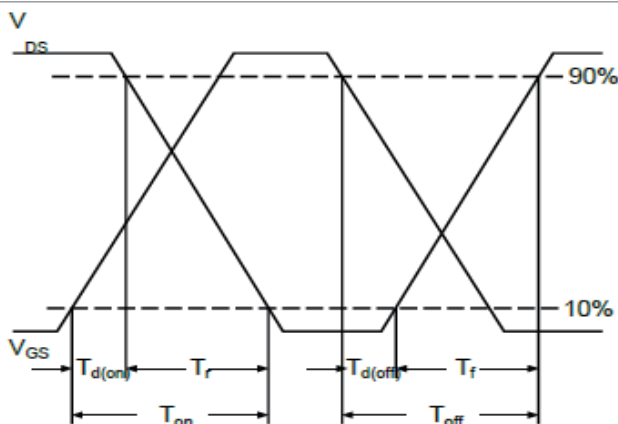
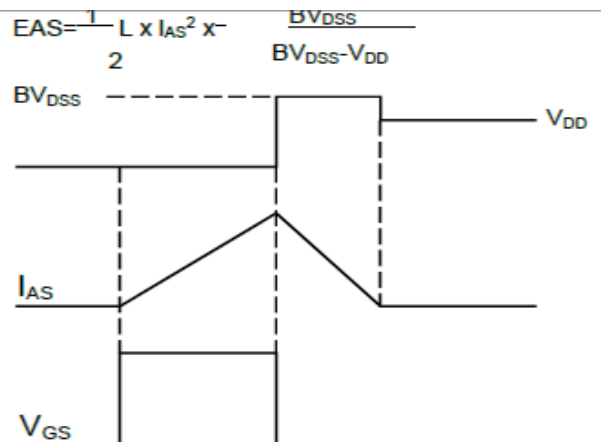
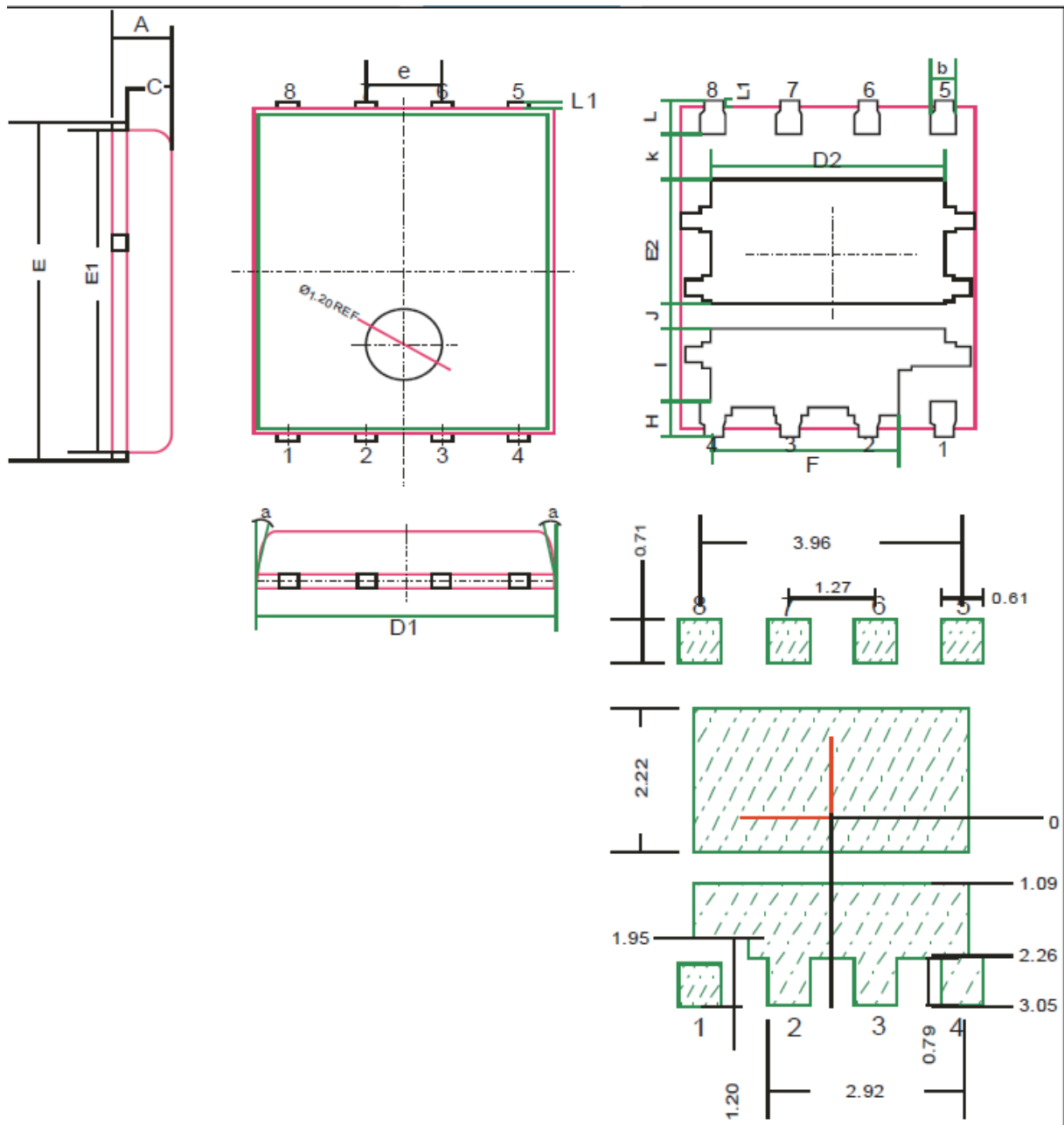


Figure.11: Unclamped Inductive Switching



Package Information PDFN5060



SYMBOL	MM			INCH			SYMBOL	MM			INCH		
	MIN	NOM	MAX	MIN	NOM	MAX		MIN	NOM	MAX	MIN	NOM	MAX
A	0.90	1.00	1.10	0.035	0.039	0.043	E1	5.70	5.75	5.80	0.224	0.226	0.228
b	0.33	0.41	0.51	0.013	0.016	0.020	E2	2.02	2.17	2.32	0.079	0.085	0.091
c	0.20	0.25	0.30	0.008	0.010	0.012	e	1.27BSC			0.05BSC		
D1	4.80	4.90	5.00	0.189	0.193	0.197	H	0.48	0.58	0.68	0.018	0.022	0.026
D2	3.61	3.81	3.96	0.142	0.150	0.156	L	0.51	0.61	0.71	0.020	0.024	0.028
L1	0.06	0.13	0.20	0.002	0.005	0.008							
E	5.90	6.00	6.10	0.232	0.236	0.240	⊘	0°	*	12°	*	10°	12°
K	0.50	*	*	0.019	*	*	J	0.40	0.50	0.60	0.015	0.019	0.023
I	1.22	1.32	1.42	0.048	0.051	0.055	F	2.87	3.07	3.22	0.112	0.12	0.126

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